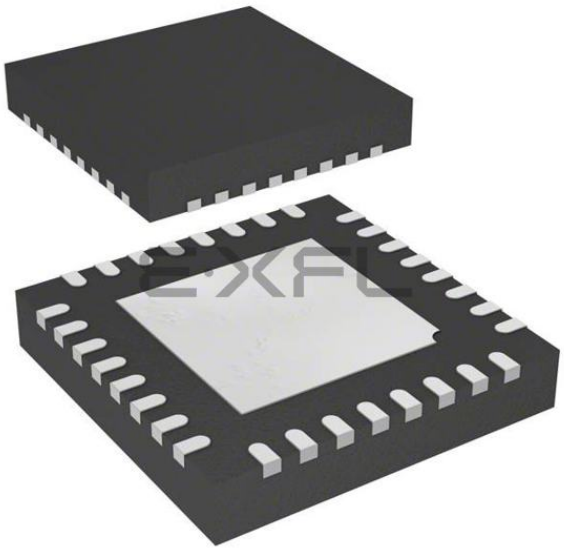

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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I²C, IrDA, LINbus, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, I²S, POR, PWM, WDT
Number of I/O	25
Program Memory Size	192KB (192K x 8)
Program Memory Type	FLASH
EEPROM Size	6K x 8
RAM Size	20K x 8
Voltage - Supply (Vcc/Vdd)	1.65V ~ 3.6V
Data Converters	A/D 10x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-UFQFN Exposed Pad
Supplier Device Package	32-UFQFPN (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l081kzu6

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2.1 Device overview

Table 1. Ultra-low-power STM32L081xx device features and peripheral counts

Peripheral		STM32L081CB	STM32L081KZ	STM32L081CZ
Flash (Kbytes)		128 Kbytes	192 Kbytes	
Data EEPROM (Kbytes)		6 Kbytes		
RAM (Kbytes)		20 Kbytes		
AES		1		
Timers	**General-purpose**	4		
	Basic	2		
	LPTIMER	1		
RTC/SYSTICK/IWDG/WWDG		1/1/1/1		
Com. interfaces	**SPI/I2S**	6(4)[1]/1	4(3)[2]/0	6(4)[1]/1
	I^2C	3	2	3
	USART	4	3	4
	LPUART	1		
GPIOs		40	25[3]	40
Clocks: HSE/LSE/HSI/MSI/LSI		1/1/1/1/1		
12-bit synchronized ADC **Number of channels**		1 13	1 10	1 13
Comparators		2		
Max. CPU frequency		32 MHz		
Operating voltage		1.8 V to 3.6 V (down to 1.65 V at power-down) with BOR option 1.65 to 3.6 V without BOR option		
Operating temperatures		Ambient temperature: –40 to +125 °C Junction temperature: –40 to +130 °C		
Packages		LQFP48	LQFP32, UFQFPN32	LQFP48

1. 4 SPI interfaces are USARTs operating in SPI master mode.
2. 3 SPI interfaces are USARTs operating in SPI master mode.
3. UFQFPN32 has 2 GPIOs less than LQFP32.

Table 5. STM32L0xx peripherals interconnect matrix (continued)

Interconnect source	Interconnect destination	Interconnect action	Run	Sleep	Low-power run	Low-power sleep	Stop
RTC	TIM21	Timer triggered by Auto wake-up	Y	Y	Y	Y	-
	LPTIM	Timer triggered by RTC event	Y	Y	Y	Y	Y
All clock source	TIMx	Clock source used as input channel for RC measurement and trimming	Y	Y	Y	Y	-
GPIO	TIMx	Timer input channel and trigger	Y	Y	Y	Y	-
	LPTIM	Timer input channel and trigger	Y	Y	Y	Y	Y
	ADC	Conversion trigger	Y	Y	Y	Y	-

3.3 ARM® Cortex®-M0+ core with MPU

The Cortex-M0+ processor is an entry-level 32-bit ARM Cortex processor designed for a broad range of embedded applications. It offers significant benefits to developers, including:

- a simple architecture that is easy to learn and program
- ultra-low power, energy-efficient operation
- excellent code density
- deterministic, high-performance interrupt handling
- upward compatibility with Cortex-M processor family
- platform security robustness, with integrated Memory Protection Unit (MPU).

The Cortex-M0+ processor is built on a highly area and power optimized 32-bit processor core, with a 2-stage pipeline Von Neumann architecture. The processor delivers exceptional energy efficiency through a small but powerful instruction set and extensively optimized design, providing high-end processing hardware including a single-cycle multiplier.

The Cortex-M0+ processor provides the exceptional performance expected of a modern 32-bit architecture, with a higher code density than other 8-bit and 16-bit microcontrollers.

Owing to its embedded ARM core, the STM32L081xx are compatible with all ARM tools and software.

Table 10. STM32L081xx I²C implementation (continued)

I2C features[1]	I2C1	I2C2	I2C3
Fast Mode Plus with 20 mA output drive I/Os (up to 1 Mbit/s)	X	X[2]	X
Independent clock	X	-	X
SMBus	X	-	X
Wakeup from STOP	X	-	X

1. X = supported.
2. See *Table 14: STM32L081xxx pin definition on page 35* for the list of I/Os that feature Fast Mode Plus capability

3.16.2 Universal synchronous/asynchronous receiver transmitter (USART)

The four USART interfaces (USART1, USART2, USART4 and USART5) are able to communicate at speeds of up to 4 Mbit/s.

They provide hardware management of the CTS, RTS and RS485 driver enable (DE) signals, multiprocessor communication mode, master synchronous communication and single-wire half-duplex communication mode. USART1 and USART2 also support SmartCard communication (ISO 7816), IrDA SIR ENDEC, LIN Master/Slave capability, auto baud rate feature and has a clock domain independent from the CPU clock, allowing to wake up the MCU from Stop mode using baudrates up to 42 Kbaud.

All USART interfaces can be served by the DMA controller.

Table 11 for the supported modes and features of USART interfaces.

Table 11. USART implementation

USART modes/features[1]	USART1 and USART2	USART4 and USART5
Hardware flow control for modem	X	X
Continuous communication using DMA	X	X
Multiprocessor communication	X	X
Synchronous mode[2]	X	X
Smartcard mode	X	-
Single-wire half-duplex communication	X	X
IrDA SIR ENDEC block	X	-
LIN mode	X	-
Dual clock domain and wakeup from Stop mode	X	-
Receiver timeout interrupt	X	-
Modbus communication	X	-
Auto baud rate detection (4 modes)	X	-
Driver Enable	X	X

1. X = supported.
2. This mode allows using the USART as an SPI master.

Table 14. STM32L081xxx pin definition

Pin number			Pin name (function after reset)	Pin type	I/O structure	Note	Alternate functions	Additional functions
LQFP32	UFQFPN32[1]	LQFP48						
1	-	1	VDD	S		-	-	-
-	-	2	PC13	I/O	FT	-	-	RTC_TAMP1/ RTC_TS/ RTC_OUT/WKUP2
2	1	3	PC14-OSC32_IN (PC14)	I/O	FT	-	-	OSC32_IN
3	2	4	PC15-OSC32_OUT (PC15)	I/O	TC	-	-	OSC32_OUT
-	-	5	PH0-OSC_IN (PH0)	I/O	TC	-	-	OSC_IN
-	-	6	PH1-OSC_OUT (PH1)	I/O	TC	-	-	OSC_OUT
4	3	7	NRST	I/O	-	-	-	-
-	4	8	VSSA	S	-	-	-	-
5	5	9	VDDA	S	-	-	-	-
6	6	10	PA0	I/O	TTa	-	TIM2_CH1, USART2_CTS, TIM2_ETR, USART4_TX, COMP1_OUT	COMP1_INM, ADC_IN0, RTC_TAMP2/WKUP1
7	7	11	PA1	I/O	FT	-	EVENTOUT, TIM2_CH2, USART2_RTS_DE, TIM21_ETR, USART4_RX	COMP1_INP, ADC_IN1
8	8	12	PA2	I/O	FT	-	TIM21_CH1, TIM2_CH3, USART2_TX, LPUART1_TX, COMP2_OUT	COMP2_INM, ADC_IN2
9	9	13	PA3	I/O	FT	-	TIM21_CH2, TIM2_CH4, USART2_RX, LPUART1_RX	COMP2_INP, ADC_IN3

Table 14. STM32L081xxx pin definition (continued)

Pin number			Pin name (function after reset)	Pin type	I/O structure	Note	Alternate functions	Additional functions
LQFP32	UFQFPN32(1)	LQFP48						
10	10	14	PA4	I/O	TC	-	SPI1_NSS, USART2_CK, TIM22_ETR	COMP1_INM, COMP2_INM, ADC_IN4
11	11	15	PA5	I/O	TC	-	SPI1_SCK, TIM2_ETR, TIM2_CH1	COMP1_INM, COMP2_INM, ADC_IN5
12	12	16	PA6	I/O	FT	-	SPI1_MISO, TIM3_CH1, LPUART1_CTS, TIM22_CH1, EVENTOUT, COMP1_OUT	ADC_IN6
13	13	17	PA7	I/O	FT	-	SPI1_MOSI, TIM3_CH2, TIM22_CH2, EVENTOUT, COMP2_OUT	ADC_IN7
14	14	18	PB0	I/O	FT	-	EVENTOUT, TIM3_CH3	ADC_IN8, VREF_OUT
15	15	19	PB1	I/O	FT	-	TIM3_CH4, LPUART1_RTS_DE	ADC_IN9, VREF_OUT
-	-	20	PB2	I/O	FT	-	LPTIM1_OUT, I2C3_SMBA	-
-	-	21	PB10	I/O	FT	-	TIM2_CH3, LPUART1_TX, SPI2_SCK, I2C2_SCL, LPUART1_RX	-
-	-	22	PB11	I/O	FT	-	EVENTOUT, TIM2_CH4, LPUART1_RX, I2C2_SDA, LPUART1_TX	-
16	16	23	VSS	S		-	-	-
17	17	24	VDD	S		-	-	-
-	-	25	PB12	I/O	FT	-	SPI2_NSS/I2S2_WS, LPUART1_RTS_DE, I2C2_SMBA, EVENTOUT	-

Table 14. STM32L081xxx pin definition (continued)

Pin number			Pin name (function after reset)	Pin type	I/O structure	Note	Alternate functions	Additional functions
LQFP32	UFQFPN32[1]	LQFP48						
26	-	39	PB3	I/O	FT	-	SPI1_SCK, TIM2_CH2, EVENTOUT, USART1_RTS_DE, USART5_TX	COMP2_INM
27	26	40	PB4	I/O	FTf	-	SPI1_MISO, TIM3_CH1, TIM22_CH1, USART1_CTS, USART5_RX, I2C3_SDA	COMP2_INP
28	27	41	PB5	I/O	FT	-	SPI1_MOSI, LPTIM1_IN1, I2C1_SMBA, TIM3_CH2/TIM22_CH2, USART1_CK, USART5_CK/USART5_RTS_DE	COMP2_INP
29	28	42	PB6	I/O	FTf	-	USART1_TX, I2C1_SCL, LPTIM1_ETR,	COMP2_INP
30	29	43	PB7	I/O	FTf	-	USART1_RX, I2C1_SDA, LPTIM1_IN2, USART4_CTS	COMP2_INP, VREF_PVD_IN
31	30	44	BOOT0	I		-	-	-
-	-	45	PB8	I/O	FTf	-	I2C1_SCL	-
-	-	46	PB9	I/O	FTf	-	EVENTOUT, I2C1_SDA, SPI2_NSS/I2S2_WS	-
32	31	47	VSS	S		-	-	-
-	32	48	VDD	S		-	-	-

1. UFQFPN32 pinout differs from other STM32 devices except STM32L07xxx and STM32L8xxx.

Table 15. Alternate functions port A

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
		SPI1/SPI2/I2S2/ USART1/2/ LPUART1/ LPTIM1 TIM2/21/22/ EVENTOUT/ SYS_AF	SPI1/SPI2/I2S2/ I2C1/TIM2/21	SPI1/SPI2/I2S2/ LPUART1/ USART5/LPTIM1/ TIM2/3/ EVENTOUT/ SYS_AF	I2C1/ EVENTOUT	I2C1/USART1/2/L PUART1/ TIM3/22/ EVENTOUT	SPI2/I2S2/I2C2/ USART1/ TIM2/21/22	I2C1/2/ LPUART1/ USART4/ UASRT5/TIM21/ EVENTOUT	I2C3/LPUART1/ COMP1/2/ TIM3
Port A	PA0	-	-	TIM2_CH1	-	USART2_CTS	TIM2_ETR	USART4_TX	COMP1_OUT
	PA1	EVENTOUT	-	TIM2_CH2	-	USART2_RTS_D E	TIM21_ETR	USART4_RX	-
	PA2	TIM21_CH1	-	TIM2_CH3	-	USART2_TX	-	LPUART1_TX	COMP2_OUT
	PA3	TIM21_CH2	-	TIM2_CH4	-	USART2_RX	-	LPUART1_RX	-
	PA4	SPI1_NSS	-	-	-	USART2_CK	TIM22_ETR	-	-
	PA5	SPI1_SCK	-	TIM2_ETR	-		TIM2_CH1	-	-
	PA6	SPI1_MISO	-	TIM3_CH1	-	LPUART1_CTS	TIM22_CH1	EVENTOUT	COMP1_OUT
	PA7	SPI1_MOSI	-	TIM3_CH2	-	-	TIM22_CH2	EVENTOUT	COMP2_OUT
	PA8	MCO	-	-	EVENTOUT	USART1_CK	-	-	I2C3_SCL
	PA9	MCO	-	-	-	USART1_TX	-	I2C1_SCL	I2C3_SMBA
	PA10	-	-	-	-	USART1_RX	-	I2C1_SDA	-
	PA11	SPI1_MISO	-	EVENTOUT	-	USART1_CTS	-	-	COMP1_OUT
	PA12	SPI1_MOSI	-	EVENTOUT	-	USART1_RTS_D E	-	-	COMP2_OUT
	PA13	SWDIO	-	-	-	-	-	LPUART1_RX	-
	PA14	SWCLK	-	-	-	USART2_TX	-	LPUART1_TX	-
	PA15	SPI1_NSS	-	TIM2_ETR	EVENTOUT	USART2_RX	TIM2_CH1	USART4_RTS_D E	-

Table 25. Current consumption in Run mode vs code type, code with data processing running from Flash memory

Symbol	Parameter	Conditions			f_{HCLK}	Typ	Unit
I_{DD} (Run from Flash memory)	Supply current in Run mode, code executed from Flash memory	f_{HSE} = f_{HCLK} up to 16 MHz included, f_{HSE} = f_{HCLK}/2 above 16 MHz (PLL on)(1)	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	Dhrystone	4 MHz	650	µA
				CoreMark		655	
				Fibonacci		485	
				while(1)		385	
				while(1), 1WS, prefetch off		375	
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	Dhrystone	32 MHz	6,65	mA
				CoreMark		6,9	
				Fibonacci		6,75	
				while(1)		5,8	
				while(1), prefetch off		5,5	

1. Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

Figure 11. I_{DD} vs V_{DD}, at T_A= 25/55/85/105 °C, Run mode, code running from Flash memory, Range 2, HSE, 1WS

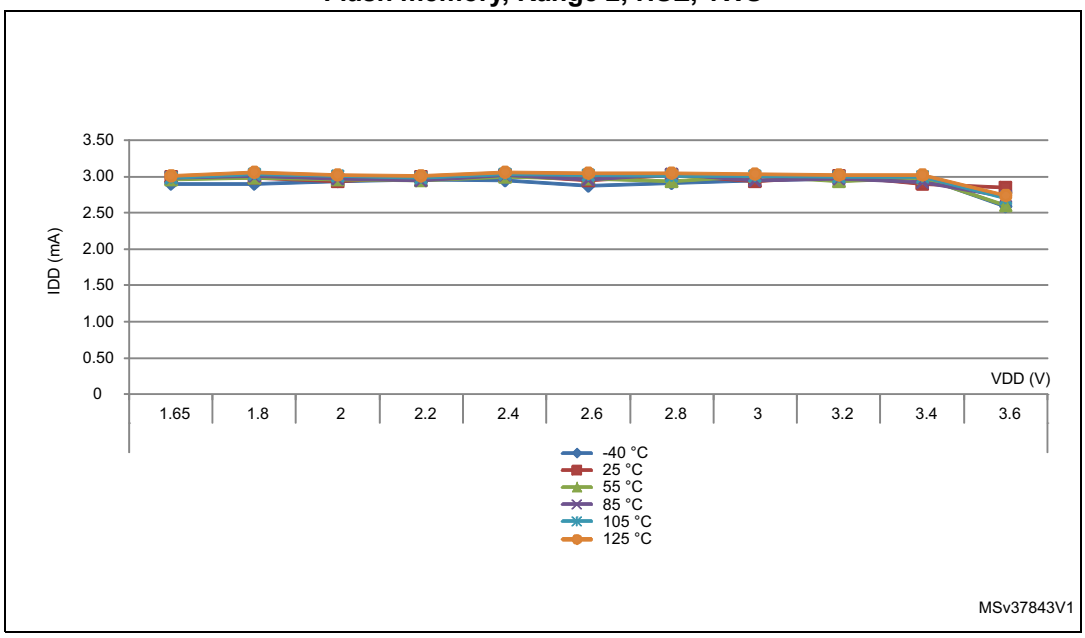


Table 28. Current consumption in Sleep mode

Symbol	Parameter	Condition		f_{HCLK} (MHz)	Typ	Max(1)	Unit
I_{DD} (Sleep)	Supply current in Sleep mode, Flash memory switched OFF	f_{HSE} = f_{HCLK} up to 16 MHz included, f_{HSE} = f_{HCLK}/2 above 16 MHz (PLL ON)(2)	Range3, Vcore=1.2 V VOS[1:0]=11	1	43,5	110	µA
				2	72	140	
				4	130	200	
			Range2, Vcore=1.5 V VOS[1:0]=10	4	160	220	
				8	305	380	
				16	590	690	
			Range1, Vcore=1.8 V VOS[1:0]=01	8	370	460	
				16	715	840	
				32	1650	2000	
		MSI clock	Range3, Vcore=1.2 V VOS[1:0]=11	0,065	18	93	
				0,524	31,5	110	
				4,2	140	230	
		HSI clock source (16 MHz)	Range2, Vcore=1.5 V VOS[1:0]=10	16	665	850	
			Range1, Vcore=1.8 V VOS[1:0]=01	32	1750	2100	
	Supply current in Sleep mode, Flash memory switched ON	f_{HSE} = f_{HCLK} up to 16MHz included, f_{HSE} = f_{HCLK}/2 above 16 MHz (PLL ON)(2)	Range3, Vcore=1.2 V VOS[1:0]=11	1	57,5	130	
				2	84	160	
				4	150	220	
			Range2, Vcore=1.5 V VOS[1:0]=10	4	170	240	
				8	315	400	
				16	605	710	
			Range1, Vcore=1.8 V VOS[1:0]=01	8	380	470	
				16	730	860	
				32	1650	2000	
		MSI clock	Range3, Vcore=1.2 V VOS[1:0]=11	0,065	29,5	110	
				0,524	44,5	120	
				4,2	150	240	
		HSI clock source (16MHz)	Range2, Vcore=1.5 V VOS[1:0]=10	16	680	930	
			Range1, Vcore=1.8 V VOS[1:0]=01	32	1750	2200	

1. Guaranteed by characterization results at 125 °C, unless otherwise specified.

Figure 15. I_{DD} vs V_{DD}, at T_A= 25/55/85/105/125 °C, Stop mode with RTC disabled, all clocks off

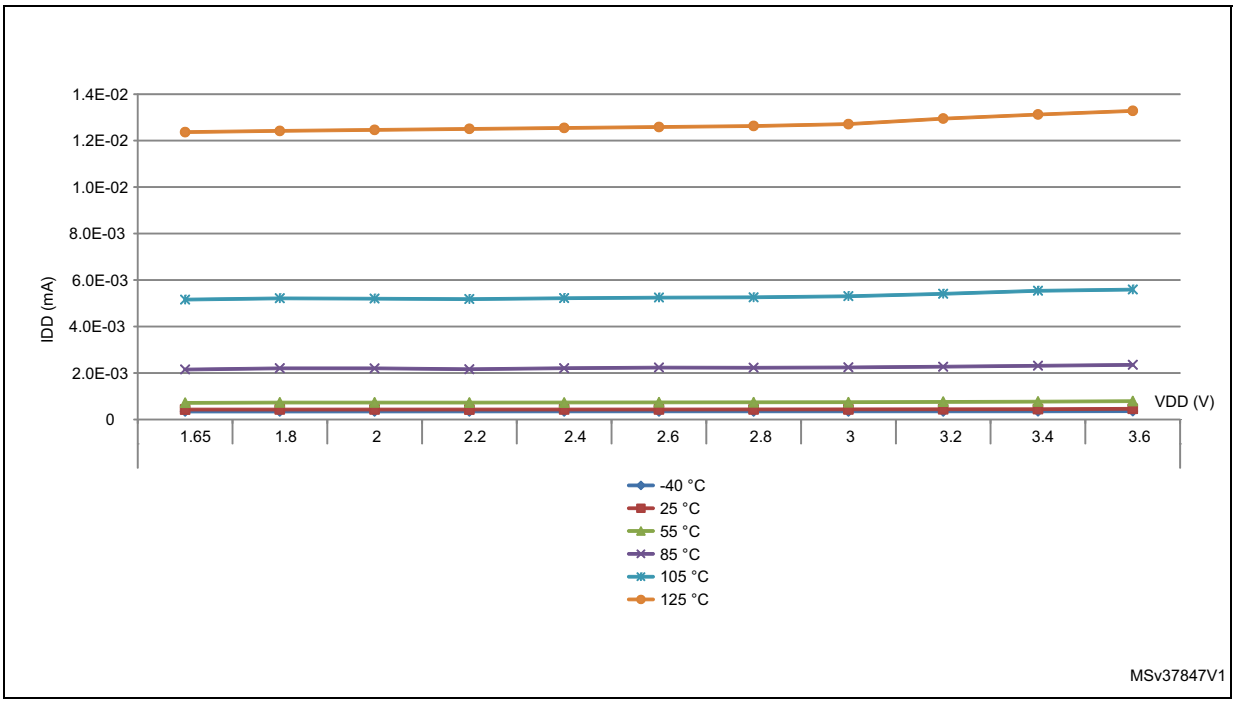


Table 32. Typical and maximum current consumptions in Standby mode

Symbol	Parameter	Conditions		Typ	Max(1)	Unit
I_{DD} (Standby)	Supply current in Standby mode	Independent watchdog and LSI enabled	T_A = − 40 to 25°C	0,855	1,70	µA
			T_A = 55 °C	-	2,90	
			T_A= 85 °C	-	3,30	
			T_A = 105 °C	-	4,10	
			T_A = 125 °C	-	8,50	
		Independent watchdog and LSI off	T_A = − 40 to 25°C	0,29	0,60	
			T_A = 55 °C	0,32	1,20	
			T_A = 85 °C	0,5	2,30	
			T_A = 105 °C	0,94	3,00	
			T_A = 125 °C	2,6	7,00	

1. Guaranteed by characterization results at 125 °C, unless otherwise specified

On-chip peripheral current consumption

The current consumption of the on-chip peripherals is given in the following tables. The MCU is placed under the following conditions:

- all I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load)
- all peripherals are disabled unless otherwise mentioned
- the given value is calculated by measuring the current consumption
  - with all peripherals clocked off
  - with only one peripheral clocked on

Table 34. Peripheral current consumption in Run or Sleep mode(1)

Peripheral		Typical consumption, V_{DD} = 3.0 V, T_A = 25 °C				Unit
		Range 1, V_{CORE}=1.8 V VOS[1:0] = 01	Range 2, V_{CORE}=1.5 V VOS[1:0] = 10	Range 3, V_{CORE}=1.2 V VOS[1:0] = 11	Low-power sleep and run	
APB1	CRS	2.5	2	2	2	µA/MHz (f_{HCLK})
	I2C1	11	9.5	7.5	9	
	I2C3	11	9	7	9	
	LPTIM1	10	8.5	6.5	8	
	LPUART1	8	6.5	5.5	6	
	SPI2	9	4.5	3.5	4	
	USART2	14.5	12	9.5	11	
	USART4	5	4	3	5	
	USART5	5	4	3	5	
	TIM2	10.5	8.5	7	9	
	TIM3	12	10	8	11	
	TIM6	3.5	3	2.5	2	
	TIM7	3.5	3	2.5	2	
	WWDG	3	2	2	2	
APB2	ADC1(2)	5.5	5	3.5	4	µA/MHz (f_{HCLK})
	SPI1	4	3	3	2.5	
	USART1	14.5	11.5	9.5	12	
	TIM21	7.5	6	5	5.5	
	TIM22	7	6	5	6	
	FIREWALL	1.5	1	1	0.5	
	DBGMCU	1.5	1	1	0.5	
	SYSCFG	2.5	2	2	1.5	

6.3.7 Internal clock source characteristics

The parameters given in *Table 41* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 20*.

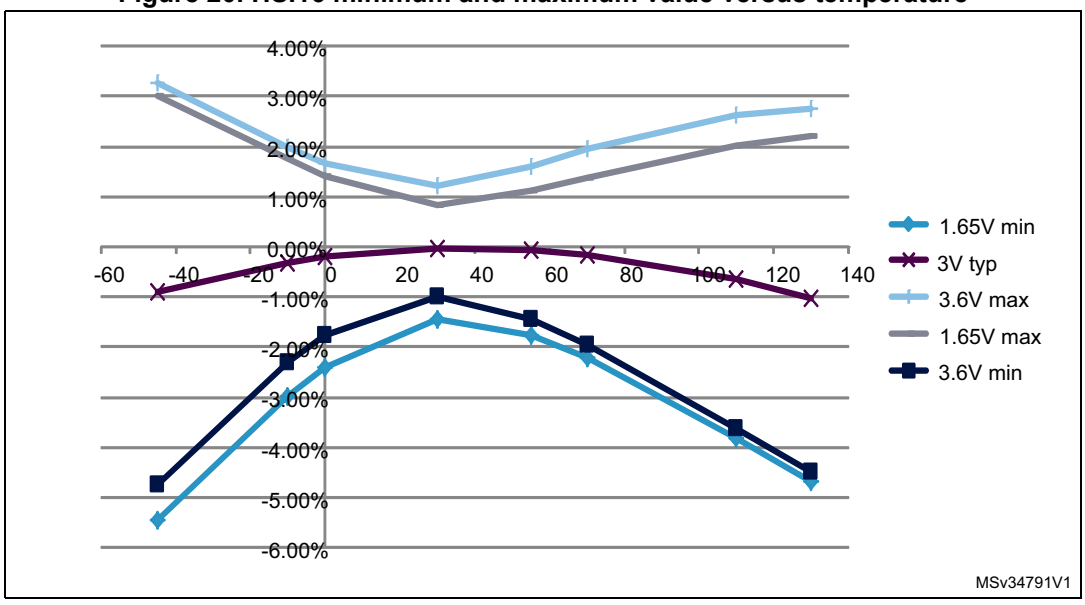
High-speed internal 16 MHz (HSI16) RC oscillator

Table 41. 16 MHz HSI16 oscillator characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSI16}	Frequency	V_{DD} = 3.0 V	-	16	-	MHz
$_{TRIM}$(1)(2)	HSI16 user-trimmed resolution	Trimming code is not a multiple of 16	-	± 0.4	0.7	%
		Trimming code is a multiple of 16	-	-	± 1.5	%
ACC_{HSI16}(2)	Accuracy of the factory-calibrated HSI16 oscillator	V_{DDA} = 3.0 V, T_A = 25 °C	-1(3)	-	1(3)	%
		V_{DDA} = 3.0 V, T_A = 0 to 55 °C	-1.5	-	1.5	%
		V_{DDA} = 3.0 V, T_A = -10 to 70 °C	-2	-	2	%
		V_{DDA} = 3.0 V, T_A = -10 to 85 °C	-2.5	-	2	%
		V_{DDA} = 3.0 V, T_A = -10 to 105 °C	-4	-	2	%
		V_{DDA} = 1.65 V to 3.6 V T_A = − 40 to 125 °C	-5.45	-	3.25	%
$t_{SU(HSI16)}$(2)	HSI16 oscillator startup time	-	-	3.7	6	µs
$I_{DD(HSI16)}$(2)	HSI16 oscillator power consumption	-	-	100	140	µA

1. The trimming step differs depending on the trimming code. It is usually negative on the codes which are multiples of 16 (0x00, 0x10, 0x20, 0x30...0xE0).
2. Guaranteed by characterization results.
3. Guaranteed by test in production.

Figure 20. HSI16 minimum and maximum value versus temperature



Low-speed internal (LSI) RC oscillator

Table 42. LSI oscillator characteristics

Symbol	Parameter	Min	Typ	Max	Unit
f_{LSI}(1)	LSI frequency	26	38	56	kHz
D_{LSI}(2)	LSI oscillator frequency drift 0°C ≤ T_A ≤ 85°C	-10	-	4	%
$t_{su(LSI)}$(3)	LSI oscillator startup time	-	-	200	µs
$I_{DD(LSI)}$(3)	LSI oscillator power consumption	-	400	510	nA

1. Guaranteed by test in production.
2. This is a deviation for an individual part, once the initial frequency has been measured.
3. Guaranteed by design.

Multi-speed internal (MSI) RC oscillator

Table 43. MSI oscillator characteristics

Symbol	Parameter	Condition	Typ	Max	Unit
f_{MSI}	Frequency after factory calibration, done at V_{DD}= 3.3 V and T_A = 25 °C	MSI range 0	65.5	-	kHz
		MSI range 1	131	-	
		MSI range 2	262	-	
		MSI range 3	524	-	
		MSI range 4	1.05	-	MHz
		MSI range 5	2.1	-	
		MSI range 6	4.2	-	
ACC_{MSI}	Frequency error after factory calibration	-	±0.5	-	%
$D_{TEMP(MSI)}$(1)	MSI oscillator frequency drift 0 °C ≤ T_A ≤ 85 °C	-	±3	-	%
	MSI oscillator frequency drift V_{DD} = 3.3 V, − 40 °C ≤ T_A ≤ 110 °C	MSI range 0	− 8.9	+7.0	
		MSI range 1	− 7.1	+5.0	
		MSI range 2	− 6.4	+4.0	
		MSI range 3	− 6.2	+3.0	
		MSI range 4	− 5.2	+3.0	
		MSI range 5	− 4.8	+2.0	
		MSI range 6	− 4.7	+2.0	
$D_{VOLT(MSI)}$(1)	MSI oscillator frequency drift 1.65 V ≤ V_{DD} ≤ 3.6 V, T_A = 25 °C	-	-	2.5	%/V

Output voltage levels

Unless otherwise specified, the parameters given in *Table 54* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 20*. All I/Os are CMOS and TTL compliant.

Table 54. Output voltage characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
V_{OL}(1)	Output low level voltage for an I/O pin	CMOS port(2), I_{IO} = +8 mA 2.7 V ≤ V_{DD} ≤ 3.6 V	-	0.4	V
V_{OH}(3)	Output high level voltage for an I/O pin		V_{DD}-0.4	-	
V_{OL} (1)	Output low level voltage for an I/O pin	TTL port(2), I_{IO} =+ 8 mA 2.7 V ≤ V_{DD} ≤ 3.6 V	-	0.4	
V_{OH} (3)(4)	Output high level voltage for an I/O pin	TTL port(2), I_{IO} = -6 mA 2.7 V ≤ V_{DD} ≤ 3.6 V	2.4	-	
V_{OL}(1)(4)	Output low level voltage for an I/O pin	I_{IO} = +15 mA 2.7 V ≤ V_{DD} ≤ 3.6 V	-	1.3	
V_{OH}(3)(4)	Output high level voltage for an I/O pin	I_{IO} = -15 mA 2.7 V ≤ V_{DD} ≤ 3.6 V	V_{DD}-1.3	-	
V_{OL}(1)(4)	Output low level voltage for an I/O pin	I_{IO} = +4 mA 1.65 V ≤ V_{DD} < 3.6 V	-	0.45	
V_{OH}(3)(4)	Output high level voltage for an I/O pin	I_{IO} = -4 mA 1.65 V ≤ V_{DD} ≤ 3.6 V	V_{DD}-0.45	-	
V_{OLFM+}(1)(4)	Output low level voltage for an FTf I/O pin in Fm+ mode	I_{IO} = 20 mA 2.7 V ≤ V_{DD} ≤ 3.6 V	-	0.4	
		I_{IO} = 10 mA 1.65 V ≤ V_{DD} ≤ 3.6 V	-	0.4	

1. The I_{IO} current sunk by the device must always respect the absolute maximum rating specified in *Table 18*. The sum of the currents sunk by all the I/Os (I/O ports and control pins) must always be respected and must not exceed $\Sigma I_{IO(PIN)}$.
2. TTL and CMOS outputs are compatible with JEDEC standards JESD36 and JESD52.
3. The I_{IO} current sourced by the device must always respect the absolute maximum rating specified in *Table 18*. The sum of the currents sourced by all the I/Os (I/O ports and control pins) must always be respected and must not exceed $\Sigma I_{IO(PIN)}$.
4. Guaranteed by characterization results.

Table 57. ADC characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_{CAL}(3)(5)	Calibration time	f_{ADC} = 16 MHz		5.2		µs
		-		83		$1/f_{ADC}$
$W_{LATENCY}$(6)	ADC_DR register write latency	ADC clock = HSI16	1.5 ADC cycles + 2 f_{PCLK} cycles	-	1.5 ADC cycles + 3 f_{PCLK} cycles	-
		ADC clock = PCLK/2	-	4.5	-	f_{PCLK} cycle
		ADC clock = PCLK/4	-	8.5	-	f_{PCLK} cycle
t_{latr}(3)	Trigger conversion latency	f_{ADC} = f_{PCLK}/2 = 16 MHz		0.266		µs
		f_{ADC} = f_{PCLK}/2		8.5		$1/f_{PCLK}$
		f_{ADC} = f_{PCLK}/4 = 8 MHz		0.516		µs
		f_{ADC} = f_{PCLK}/4		16.5		$1/f_{PCLK}$
		f_{ADC} = f_{HSI16} = 16 MHz	0.252	-	0.260	µs
$Jitter_{ADC}$	ADC jitter on trigger conversion	f_{ADC} = f_{HSI16}	-	1	-	$1/f_{HSI16}$
t_S(3)	Sampling time	f_{ADC} = 16 MHz	0.093	-	10.03	µs
		-	1.5	-	160.5	$1/f_{ADC}$
t_{UP_LDO}(3)(5)	Internal LDO power-up time	-	-	-	10	µs
t_{STAB}(3)(5)	ADC stabilization time	-		14		$1/f_{ADC}$
t_{ConV}(3)	Total conversion time (including sampling time)	f_{ADC} = 16 MHz, 12-bit resolution	0.875	-	10.81	µs
		12-bit resolution	14 to 173 (t_S for sampling +12.5 for successive approximation)			$1/f_{ADC}$

1. V_{DDA} minimum value can be decreased in specific temperature conditions. Refer to *Table 58: RAIN max for fADC = 16 MHz*.
2. A current consumption proportional to the APB clock frequency has to be added (see *Table 34: Peripheral current consumption in Run or Sleep mode*).
3. Guaranteed by design.
4. Standard channels have an extra protection resistance which depends on supply voltage. Refer to *Table 58: RAIN max for fADC = 16 MHz*.
5. This parameter only includes the ADC timing. It does not take into account register access latency.
6. This parameter specifies the latency to transfer the conversion result into the ADC_DR register. EOC bit is set to indicate the conversion is complete and has the same latency.

Equation 1: R_{AIN} max formula

$$R_{AIN} < \frac{T_S}{f_{ADC} \times C_{ADC} \times \ln(2^{N+2})} - R_{ADC}$$

The simplified formula above (*Equation 1*) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. Here N = 12 (from 12-bit resolution).

Table 58. R_{AIN} max for f_{ADC} = 16 MHz(1)

T_s (cycles)	t_S (µs)	R_{AIN} max for fast channels (kΩ)	R_{AIN} max for standard channels (kΩ)						
			V_{DD} > 2.7 V	V_{DD} > 2.4 V	V_{DD} > 2.0 V	V_{DD} > 1.8 V	V_{DD} > 1.75 V	V_{DD} > 1.65 V and T_A > –10 °C	V_{DD} > 1.65 V and T_A > 25 °C
1.5	0.09	0.5	< 0.1	NA	NA	NA	NA	NA	NA
3.5	0.22	1	0.2	< 0.1	NA	NA	NA	NA	NA
7.5	0.47	2.5	1.7	1.5	< 0.1	NA	NA	NA	NA
12.5	0.78	4	3.2	3	1	NA	NA	NA	NA
19.5	1.22	6.5	5.7	5.5	3.5	NA	NA	NA	< 0.1
39.5	2.47	13	12.2	12	10	NA	NA	NA	5
79.5	4.97	27	26.2	26	24	< 0.1	NA	NA	19
160.5	10.03	50	49.2	49	47	32	< 0.1	< 0.1	42

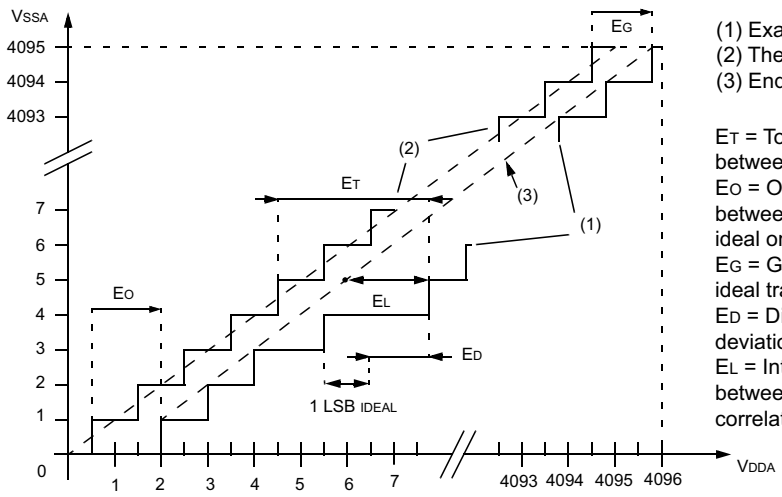
1. Guaranteed by design.

Table 59. ADC accuracy(1)(2)(3)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
ET	Total unadjusted error	1.65 V < V_{DDA} < 3.6 V, range 1/2/3	-	2	4	LSB
EO	Offset error		-	1	2.5	
EG	Gain error		-	1	2	
EL	Integral linearity error		-	1.5	2.5	
ED	Differential linearity error		-	1	1.5	
ENOB	Effective number of bits		10.2	11		bits
	Effective number of bits (16-bit mode oversampling with ratio =256)(4)		11.3	12.1	-	
SINAD	Signal-to-noise distortion		63	69	-	dB
SNR	Signal-to-noise ratio		63	69	-	
	Signal-to-noise ratio (16-bit mode oversampling with ratio =256)(4)		70	76	-	
THD	Total harmonic distortion		-	-85	-73	

1. ADC DC accuracy values are measured after internal calibration.
2. ADC Accuracy vs. Negative Injection Current: Injecting negative current on any of the standard (non-robust) analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to standard analog pins which may potentially inject negative current.
   Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in *Section 6.3.12* does not affect the ADC accuracy.
3. Better performance may be achieved in restricted V_{DDA}, frequency and temperature ranges.
4. This number is obtained by the test board without additional noise, resulting in non-optimized value for oversampling mode.

Figure 25. ADC accuracy characteristics

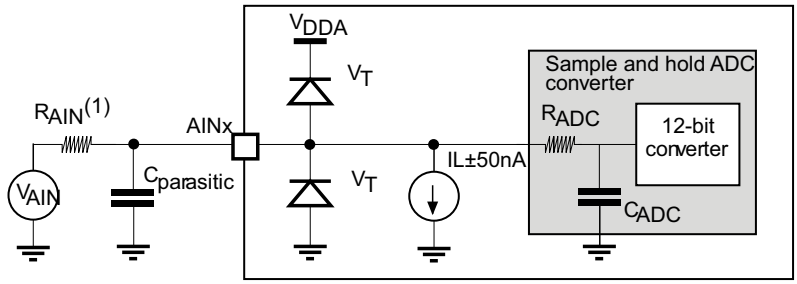


(1) Example of an actual transfer curve
(2) The ideal transfer curve
(3) End point correlation line

E_T = Total Unajusted Error: maximum deviation between the actual and ideal transfer curves.
E_O = Offset Error: maximum deviation between the first actual transition and the first ideal one.
E_G = Gain Error: deviation between the last ideal transition and the last actual one.
E_D = Differential Linearity Error: maximum deviation between actual steps and the ideal ones.
E_L = Integral Linearity Error: maximum deviation between any actual transition and the end point correlation line.

MS19880V2

Figure 26. Typical connection diagram using the ADC



MSv34712V1

1. Refer to *Table 57: ADC characteristics* for the values of R_{AIN}, R_{ADC} and C_{ADC}.
2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high $C_{parasitic}$ value will downgrade conversion accuracy. To remedy this, f_{ADC} should be reduced.

6.3.16 Temperature sensor characteristics

Table 60. Temperature sensor calibration values

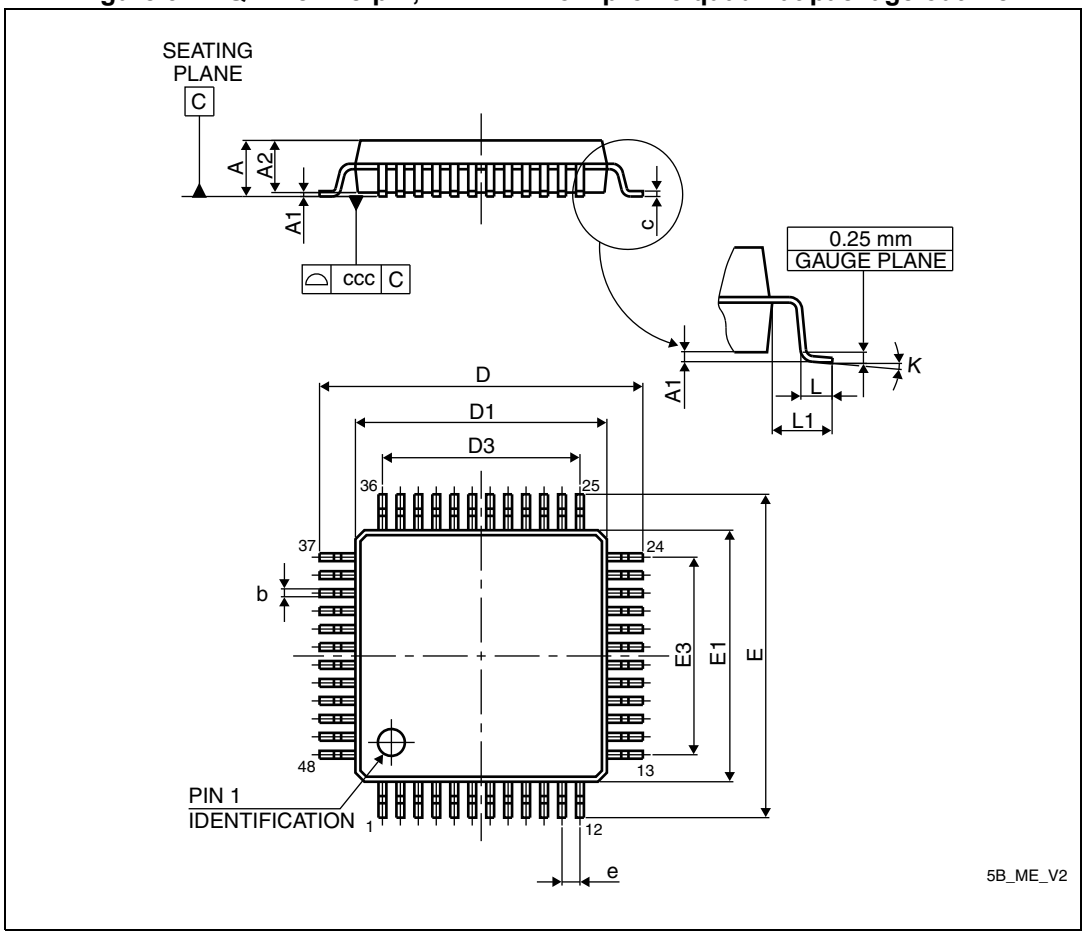
Calibration value name	Description	Memory address
TS_CAL1	TS ADC raw data acquired at temperature of 30 °C, V_{DDA}= 3 V	0x1FF8 007A - 0x1FF8 007B
TS_CAL2	TS ADC raw data acquired at temperature of 130 °C, V_{DDA}= 3 V	0x1FF8 007E - 0x1FF8 007F

7 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status *are available at www.st.com.* ECOPACK® is an ST trademark.

7.1 LQFP48 package information

Figure 32. LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package outline



1. Drawing is not to scale.

8 Part numbering

Table 75. STM32L081xx ordering information scheme

Example: STM32 L 081 C Z T 6 D TR

Device family

STM32 = ARM-based 32-bit microcontroller

Product type

L = Low power

Device subfamily

081 = Access line + AES

Pin count

K = 32 pins

C = 48/49 pins

Flash memory size

B = 128 Kbytes

Z = 192 Kbytes

Package

T = LQFP

U = UFQFPN

Temperature range

6 = Industrial temperature range, –40 to 85 °C

7 = Industrial temperature range, –40 to 105 °C

3 = Industrial temperature range, –40 to 125 °C

Options

No character = V_{DD} range: 1.8 to 3.6 V and BOR enabled

D = V_{DD} range: 1.65 to 3.6 V and BOR disabled

Packing

TR = tape and reel

No character = tray or tube

For a list of available options (speed, package, etc.) or for further information on any aspect of this device, please contact your nearest ST sales office.